

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No	
Filing Date	
Inventorship	
Assignee	
Group Art Unit	
Examiner	
Attorney's Docket No	MI22-2194
Title: Methods of Forming Material on a S	Substrate, and a Method of Forming a
Field Effect Transistor Gate Oxide of	on a Substrate

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - See Attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. Copies of the cited art are not included (1276 Off. Gaz. Pat. Off 55, 05 August 2003). No admission is made regarding whether all the submitted references are prior art.

This Supplemental Information Disclosure Statement is being filed within three months of the filing date of the application or before the mailing of a first Office Action on the merits, whichever occurs last. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 1-12-05

Mark S. Matkin Reg. No. 32,268

. Filing Date If Appropriate



*Examiner's Initials

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

(Use several sheets if necessary)

Date

ATTY. DOCKET NO. MI22-2194

SERIAL NO. 10/636,038

APPLICANT: Gurtej S. Sandhu

Name

FILING DATE August 6, 2003

Class

GROUP 2824

Subclass

LIST OF ART CITED BY APPLICANT

AA

AB

DOCUMENTS

Document Number

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OTHER RE	AL			rtinent Pages, Etc.) ontrolled deposition of SiO ₂ and Al ₂ O ₃	using ABAB	binary rea	action seq	uence
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